Designer's™ Data Sheet
High Current Lead Mounted Rectifiers

- Current Capacity Comparable to Chassis Mounted Rectifiers
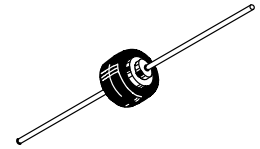- Very High Surge Capacity
- Insulated Case

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 2.5 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Lead is Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Polarity: Cathode Polarity Band
- Shipped 1000 units per plastic bag. Available Tape and Reeled, 800 units per reel by adding a "RL" suffix to the part number
- Marking: R750, R751, R752, R754, R758, R760

MR750
MR751
MR752
MR754
MR756
MR758
MR760

MR754 and MR756 are
Preferred Devices

**HIGH CURRENT
LEAD MOUNTED
SILICON RECTIFIERS
50–1000 VOLTS
DIFFUSED JUNCTION**

CASE 194–04

MAXIMUM RATINGS

Characteristic	Symbol	MR750	MR751	MR752	MR754	MR756	MR758	MR760	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
Non–Repetitive Peak Reverse Voltage (Halfwave, single phase, 60 Hz peak)	V_{RSM}	60	120	240	480	720	960	1200	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz) See Figures 5 and 6	I_O	22 (T_L = 60°C, 1/8″ Lead Lengths) 6.0 (T_A = 60°C, P.C. Board mounting)							Amps
Non–Repetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}	400 (for 1 cycle)							Amps
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175							°C

ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage Drop (i_F = 100 Amps, T_J = 25°C)	v_F	1.25	Volts
Maximum Forward Voltage Drop (I_F = 6.0 Amps, T_A = 25°C, 3/8″ leads)	V_F	0.90	Volts
Maximum Reverse Current T_J = 25°C (Rated dc Voltage) T_J = 100°C	I_R	25 1.0	μA mA

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Preferred devices are Motorola recommended choices for future use and best overall value.

Rev 2

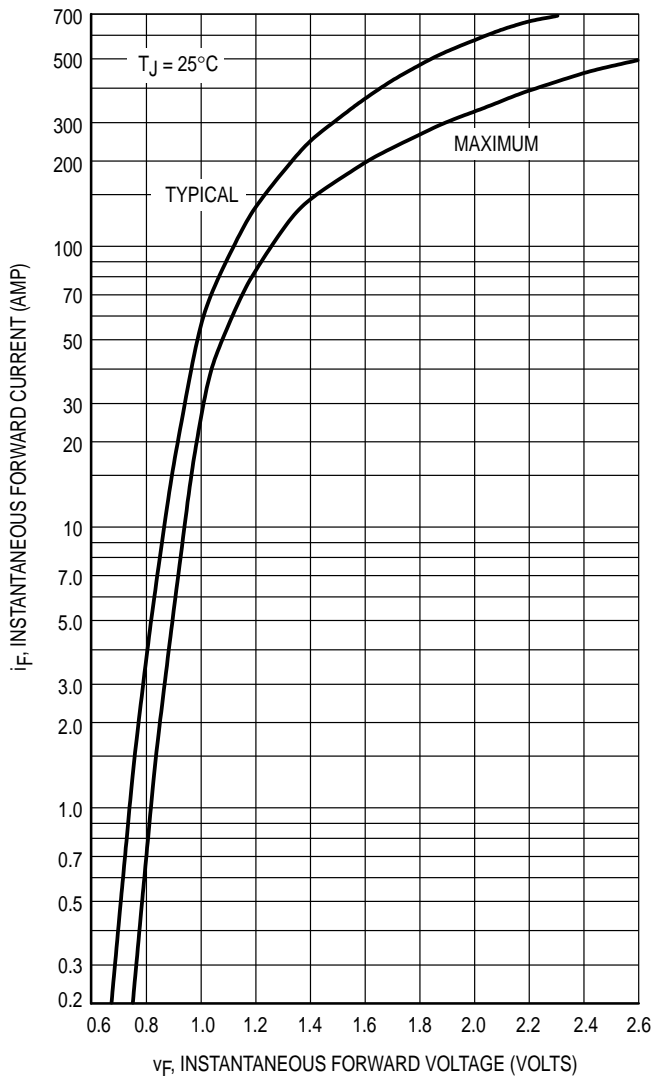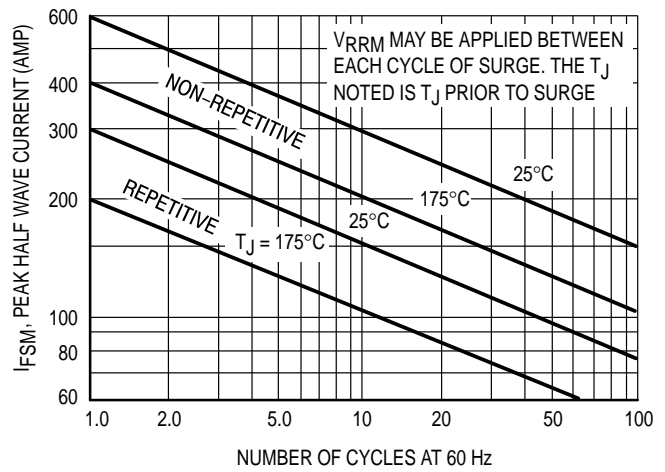## MR750 MR751 MR752 MR754 MR756 MR758 MR760
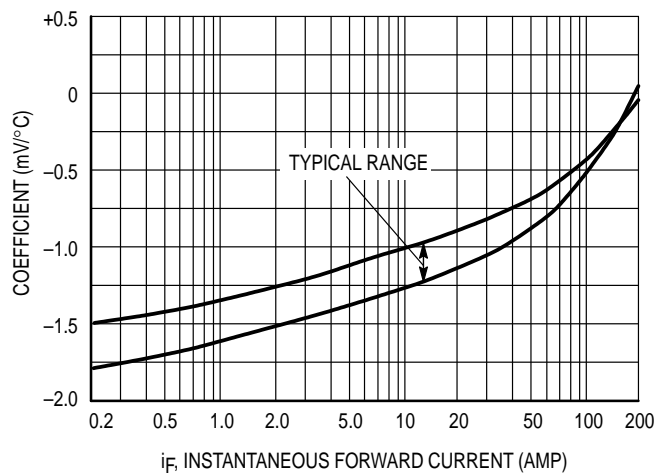

Figure 1. Forward Voltage

Figure 2. Maximum Surge Capability

Figure 3. Forward Voltage Temperature Coefficient

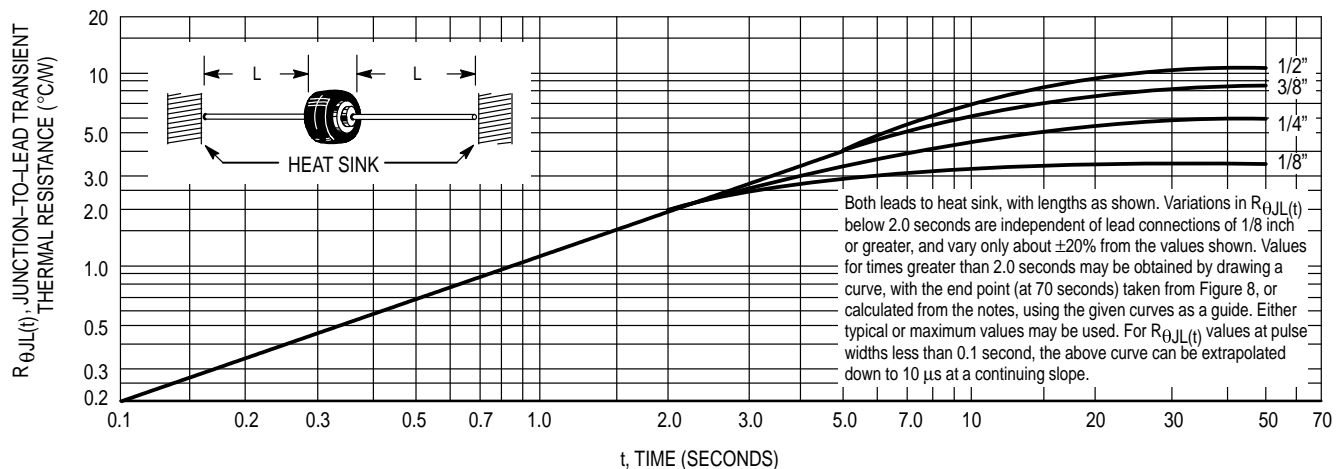Both leads to heat sink, with lengths as shown. Variations in $R_{\theta JL(t)}$ below 2.0 seconds are independent of lead connections of 1/8 inch or greater, and vary only about ±20% from the values shown. Values for times greater than 2.0 seconds may be obtained by drawing a curve, with the end point (at 70 seconds) taken from Figure 8, or calculated from the notes, using the given curves as a guide. Either typical or maximum values may be used. For $R_{\theta JL(t)}$ values at pulse widths less than 0.1 second, the above curve can be extrapolated down to 10 µs at a continuing slope.
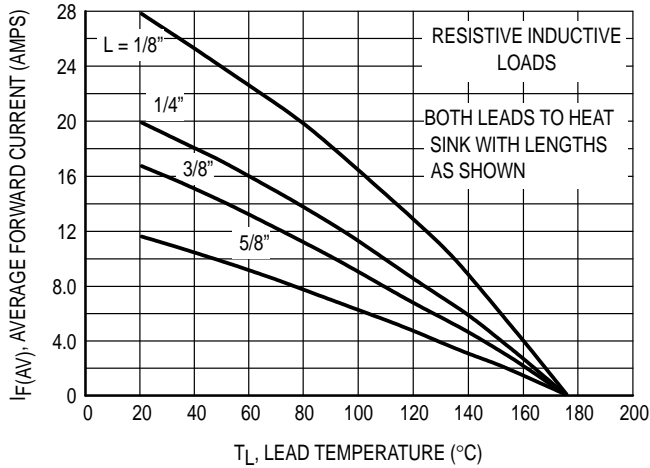
Figure 4. Typical Transient Thermal Resistance
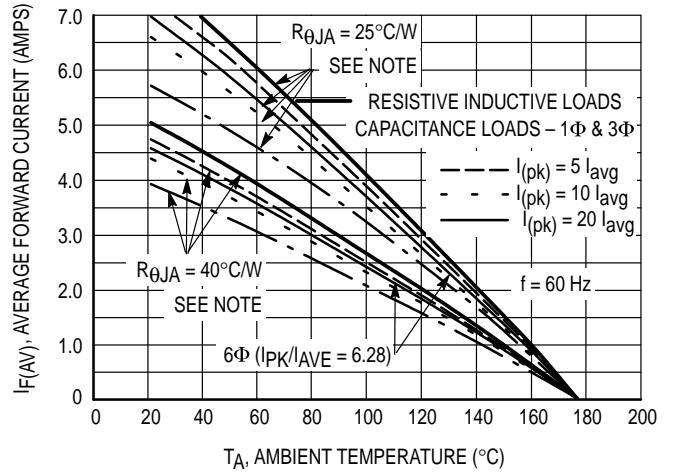
Figure 5. Maximum Current Ratings
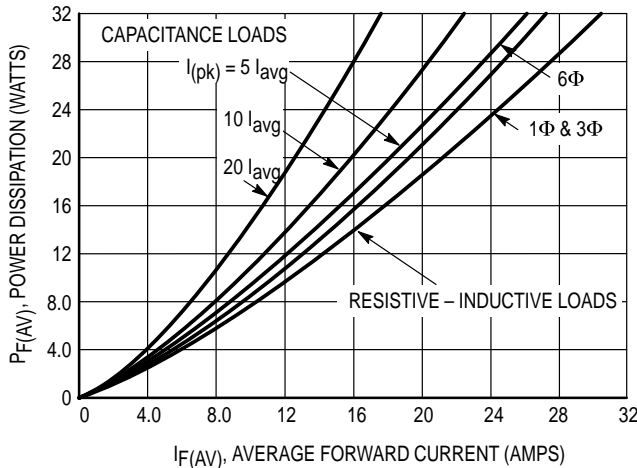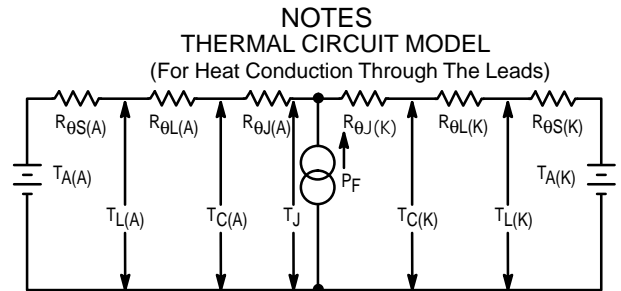

Figure 6. Maximum Current Ratings

Figure 7. Power Dissipation

NOTES
THERMAL CIRCUIT MODEL
(For Heat Conduction Through The Leads)

Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. Lowest values occur when one side of the rectifier is brought as close as possible to the heat sink as shown below. Terms in the model signify:

T_A = Ambient Temperature $\quad$ T_C = Case Temperature
T_L = Lead Temperature $\quad$ T_J = Junction Temperature
$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
$R_{\theta J}$ = Thermal Resistance, Junction to Case
P_F = Power Dissipation
(Subscripts A and K refer to anode and cathode sides, respectively.)
Values for thermal resistance components are:
$R_{\theta L}$ = 40°C/W/in. Typically and 44°C/W/in Maximum.
$R_{\theta J}$ = 2°C/W typically and 4°C/W Maximum.

Since $R_{\theta J}$ is so low, measurements of the case temperature, T_C, will be approximately equal to junction temperature in practical lead mounted applications. When used as a 60 Hz rectifierm the slow thermal response holds $T_{J(PK)}$ close to $T_{J(AVG)}$. Therefore maximum lead temperature may be found from: $T_L = 175° - R_{\theta JL} P_F$. P_F may be found from Figure 7.

The recommended method of mounting to a P.C. board is shown on the sketch, where $R_{\theta JA}$ is approximately 25°C/W for a 1–1/2" x 1–1/2" copper surface area. Values of 40°C/W are typical for mounting to terminal strips or P.C. boards where available surface area is small.

Board Ground Plane
Recommended mounting for half wave circuit

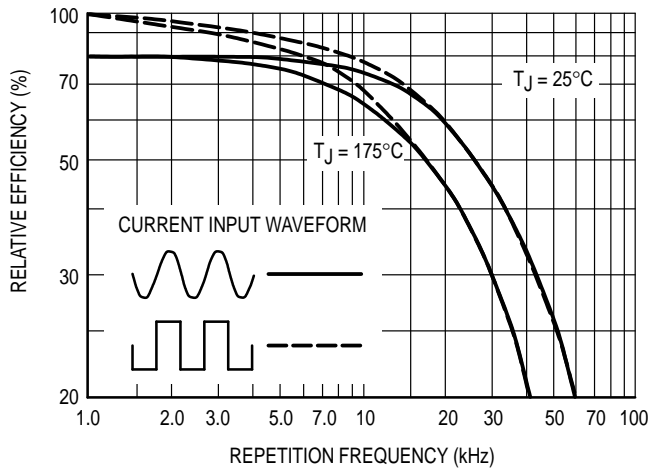Figure 8. Steady State Thermal Resistance
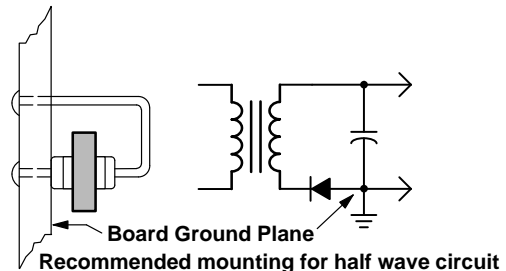
Figure 9. Rectification Efficiency
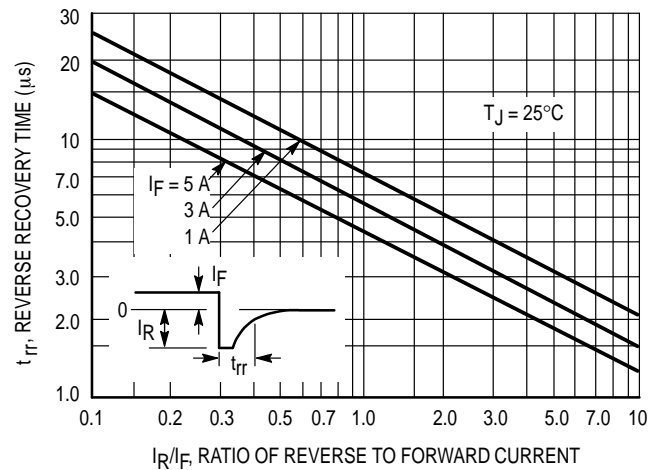

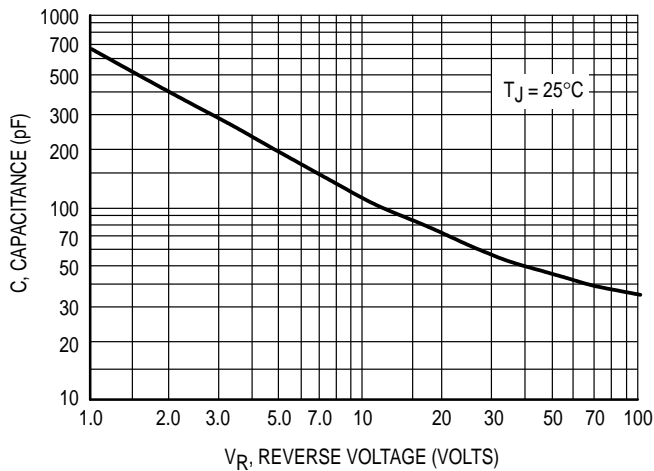**Figure 10. Reverse Recovery Time**

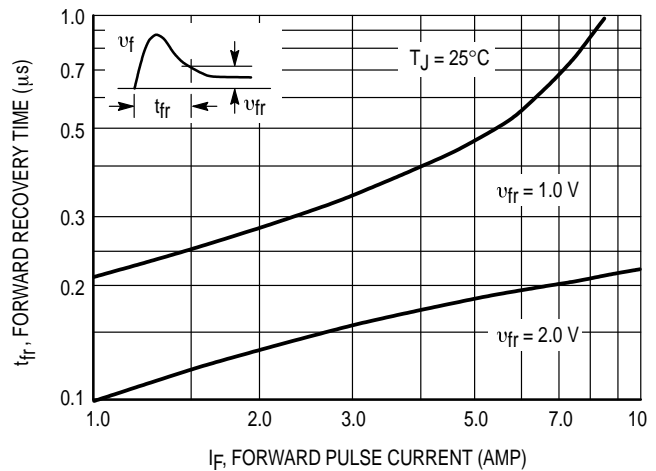
Figure 11. Junction Capacitance
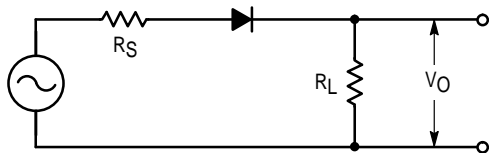

Figure 12. Forward Recovery Time

Figure 13. Single–Phase Half–Wave Rectifier Circuit

The rectification efficiency factor σ shown in Figure 9 was calculated using the formula:

$$\sigma = \frac{P_{(dc)}}{P_{(rms)}} = \frac{\dfrac{V^2{}_O(dc)}{R_L}}{\dfrac{V^2{}_O(rms)}{R_L}} \cdot 100\% = \frac{V^2{}_O(dc)}{V^2{}_O(ac) + V^2{}_O(dc)} \cdot 100\% \tag{1}$$

For a sine wave input V_m sin (wt) to the diode, assumed lossless, the maximum theoretical efficiency factor becomes:

$$\sigma_{(sine)} = \frac{\dfrac{V^2{}_m}{\pi^2 R_L}}{\dfrac{V^2{}_m}{4R_L}} \cdot 100\% = \frac{4}{\pi^2} \cdot 100\% = 40.6\% \tag{2}$$

For a square wave input of amplitude V_m, the efficiency factor becomes:

$$\sigma_{(square)} = \frac{\dfrac{V^2{}_m}{2R_L}}{\dfrac{V^2{}_m}{R_L}} \cdot 100\% = 50\% \tag{3}$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 10) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor σ, as shown on Figure 9.

It should be emphasized that Figure 9 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_O with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for Figure 9.

PACKAGE DIMENSIONS
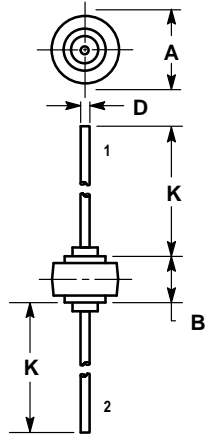
NOTES:
  1. CATHODE SYMBOL ON PACKAGE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.43	8.69	0.332	0.342
B	5.94	6.25	0.234	0.246
D	1.27	1.35	0.050	0.053
E	25.15	25.65	0.990	1.010

STYLE 1:
  PIN 1. CATHODE
      2. ANODE

CASE 194–04
ISSUE F

ASEMI semiconductor manufacturers professional operation of sepatate components,the main production and sales of rectifier seties package (DB,WOB,BR,KBPC, KBP,KBPM,GBU,GBL,KBL,KBJ,KBU);rectifier module (MDS,MTC,MDQ,QLF,SQLF);25A STD and TVS (auto commutator ~ 50A button,Cell MUR,TO-220);Schottky diodes (TO-220,TO-263,TO-251,TO-252,TO-247,TO-277 and 10A-60A) of all plastic and half plastic; glass passivated (GPP) six inch wafer,a variety of packges the parameters are described in detail in the ASEMI website. The only specified trademark is ASEMI and